Shigefusa Chichibu

List of Publications by Year
in descending order

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318 papers	11,308 citations	41258 49 h-index	35952 97 g-index
323 all docs	323 docs citations	323 times ranked	7139 citing authors

#	Article	IF	Citations
1	Reactive RF magnetron sputtering epitaxy of NiO thin films on (0001) sapphire and (100) MgO substrates. Japanese Journal of Applied Physics, 2022, 61, 025505.	0.8	3
2	Enhanced quantum efficiency of a self-organized silica mixed red phosphor CaAlSiN3:Eu. Journal of Solid State Chemistry, 2022, 309, 122968.	1.4	2
3	Dual-peak electroluminescence spectra generated from Al _n _{/12}Ga_{1-n/12}N (n = 2, 3, 4) for AlGaN-based LEDs with nonflat quantum wells. Journal Physics D: Applied Physics, 2022, 55, 255102.	1.3	3
4	Impacts of Si-doping on vacancy complex formation and their influences on deep ultraviolet luminescence dynamics in Al_xGa_{1â^'x}N films and multiple quantum wells grown by metalorganic vapor phase epitaxy. Japanese Journal of Applied Physics, 2022, 61, 050501.	0.8	4
5	Low-pressure acidic ammonothermal growth of 2-inch-diameter nearly bowing-free bulk GaN crystals. Applied Physics Express, 2022, 15, 055504.	1.1	7
6	Effect of Ultraâ€Highâ€Pressure Annealing on Defect Reactions in Ionâ€Implanted GaN Studied by Positron Annihilation. Physica Status Solidi (B): Basic Research, 2022, 259, .	0.7	7
7	Recombination dynamics of indirect excitons in hexagonal BN epilayers containing polytypic segments grown by chemical vapor deposition using carbon-free precursors. Applied Physics Letters, 2022, 120, .	1.5	2
8	(Invited) Characterization of Semiconductor Crystals Based on Omnidirectional Photoluminescence (ODPL) Spectroscopy. ECS Meeting Abstracts, 2022, MA2022-01, 1301-1301.	0.0	0
9	Boundary Conditions for Simulations of Fluid Flow and Temperature Field during Ammonothermal Crystal Growthâ€"A Machine-Learning Assisted Study of Autoclave Wall Temperature Distribution. Crystals, 2021, 11, 254.	1.0	8
10	Numerical Simulation of Ammonothermal Crystal Growth of GaNâ€"Current State, Challenges, and Prospects. Crystals, 2021, 11, 356.	1.0	16
11	Discrete AlN mole fraction of n/12 (nâ€‰=â€‰4â€“8) in Ga-rich zones functioning as electron pathways created in nonflat AlGaN layers grown on high-miscut sapphire substrates. Journal of Applied Physics, 2021, 129, 164503.	1.1	4
12	Electrical degradation and recovery of NiO/ZnO visible-light-transparent flexible solar cells. Japanese Journal of Applied Physics, 2021, 60, 064001.	0.8	0
13	Reduced nonradiative recombination rates in c-plane Al0.83In0.17N films grown on a nearly lattice-matched GaN substrate by metalorganic vapor phase epitaxy. Applied Physics Letters, 2021, 119, .	1.5	5
14	Effective neutron detection using vertical-type BGaN diodes. Journal of Applied Physics, 2021, 130, .	1.1	5
15	Facile method for the synthesis of zinc- or magnesium-doped gallium nitride powders from gallium metal. Journal of Crystal Growth, 2021, 570, 126190.	0.7	2
16	Discrete wavelengths observed in electroluminescence originating from Al1/2Ga1/2N and Al1/3Ga2/3N created in nonflat AlGaN quantum wells. Journal Physics D: Applied Physics, 2021, 54, 485107.	1.3	3
17	Innovative Techniques for Fast Growth and Fabrication of High Purity GaN Single Crystals. Springer Series in Materials Science, 2021, , 65-76.	0.4	0
18	Dopant activation process in Mg-implanted GaN studied by monoenergetic positron beam. Scientific Reports, 2021, 11, 20660.	1.6	12

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19	Improved minority carrier lifetime in p-type GaN segments prepared by vacancy-guided redistribution of Mg. Applied Physics Letters, 2021, 119, .	1.5	13
20	Vacancy complexes acting as midgap recombination centers in (Al,Ga)N semiconductors. , 2021, , .		0
21	Suppression of Green Luminescence of Mgâ€Ionâ€Implanted GaN by Subsequent Implantation of Fluorine Ions at High Temperature. Physica Status Solidi (B): Basic Research, 2020, 257, 1900554.	0.7	12
22	Reviewâ€"Defect-Tolerant Luminescent Properties of Low InN Mole Fraction In_xGa₁₋_xN Quantum Wells under the Presence of Polarization Fields. ECS Journal of Solid State Science and Technology, 2020, 9, 015016.	0.9	5
23	Spatio-time-resolved cathodoluminescence studies of wide-bandgap group-III nitride semiconductors. Japanese Journal of Applied Physics, 2020, 59, 020501.	0.8	5
24	Roles of carbon impurities and intrinsic nonradiative recombination centers on the carrier recombination processes of GaN crystals. Applied Physics Express, 2020, 13, 012004.	1.1	20
25	Theoretical analysis of photo-recycling effect on external quantum efficiency considering spatial carrier dynamics. Japanese Journal of Applied Physics, 2020, 59, SGGK02.	0.8	0
26	Self-organized micro-light-emitting diode structure for high-speed solar-blind optical wireless communications. Applied Physics Letters, 2020, 117, .	1.5	16
27	Effects of ultra-high-pressure annealing on characteristics of vacancies in Mg-implanted GaN studied using a monoenergetic positron beam. Scientific Reports, 2020, 10, 17349.	1.6	22
28	Annealing behaviors of vacancy-type defects in AlN deposited by radio-frequency sputtering and metalorganic vapor phase epitaxy studied using monoenergetic positron beams. Journal of Applied Physics, 2020, 128, .	1.1	24
29	Room-temperature cavity-polaritons in planar ZnO microcavities fabricated by a top-down process. Applied Physics Letters, 2020, 117, .	1.5	4
30	Self-formed compositional superlattices triggered by cation orderings in m-plane Al1â^'xInxN on GaN. Scientific Reports, 2020, 10, 18570.	1.6	8
31	Urbachâ€"Martienssen tail as the origin of the two-peak structure in the photoluminescence spectra for the near-band-edge emission of a freestanding GaN crystal observed by omnidirectional photoluminescence spectroscopy. Applied Physics Letters, 2020, 117, 171103.	1.5	1
32	Ammonothermal growth of 2 inch long GaN single crystals using an acidic NH₄F mineralizer in a Ag-lined autoclave. Applied Physics Express, 2020, 13, 055505.	1.1	19
33	Analyzing oxygen and silicon incorporation in GaN microstructures composed of c-planes and angled facets by confocal magneto-photoluminescence microscopy. AIP Advances, 2020, 10, 035215.	0.6	0
34	Hole capture-coefficient of intrinsic nonradiative recombination centers that commonly exist in bulk, epitaxial, and proton-irradiated ZnO. Journal of Applied Physics, 2020, 127, 215704.	1.1	6
35	Impact of high-temperature implantation of Mg ions into GaN. Japanese Journal of Applied Physics, 2020, 59, 056502.	0.8	8
36	Temperature dependence of internal quantum efficiency of radiation for the near-band-edge emission of GaN crystals quantified by omnidirectional photoluminescence spectroscopy. Applied Physics Express, 2020, 13, 105504.	1.1	3

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37	Detailed analysis of Ga-rich current pathways created in an n-Al0.7Ga0.3N layer grown on an AlN template with dense macrosteps. Applied Physics Express, 2020, 13, 124001.	1.1	7
38	Correlation between the internal quantum efficiency and photoluminescence lifetime of the near-band-edge emission in a ZnO single crystal grown by the hydrothermal method. Applied Physics Express, 2020, 13, 121005.	1.1	2
39	Control of vacancy-type defects in Mg implanted GaN studied by positron annihilation spectroscopy. , 2020, , .		0
40	Characterization of a self-organized deep-ultraviolet micro-light-emitting diode structure for high-speed solar-blind optical wireless communications. , 2020, , .		2
41	Internal quantum efficiency of radiation in a bulk CH3NH3PbBr3 perovskite crystal quantified by using the omnidirectional photoluminescence spectroscopy. APL Materials, 2019, 7, .	2.2	24
42	Room temperature photoluminescence lifetime for the near-band-edge emission of epitaxial and ion-implanted GaN on GaN structures. Japanese Journal of Applied Physics, 2019, 58, SC0802.	0.8	25
43	Impact of growth temperature on the structural properties of BGaN films grown by metal-organic vapor phase epitaxy using trimethylboron. Japanese Journal of Applied Physics, 2019, 58, SC1042.	0.8	6
44	Theoretical Formulation of Experimentally Observed Quantum Efficiency ofÂRadiation in Semiconducting Crystal. Physical Review Applied, 2019, 12, .	1.5	3
45	Quantification of the quantum efficiency of radiation of a freestanding GaN crystal placed outside an integrating sphere. Applied Physics Express, 2019, 12, 062010.	1.1	6
46	Annealing Behavior of Vacancyâ€Type Defects in Mgâ€•and Hâ€Implanted GaN Studied Using Monoenergetic Positron Beams. Physica Status Solidi (B): Basic Research, 2019, 256, 1900104.	0.7	27
47	Comparison of Al _x Ga_{1â^'x}N multiple quantum wells designed for 265 and 285 nm deep-ultraviolet LEDs grown on AlN templates having macrosteps. Applied Physics Express, 2019, 12, 064009.	1.1	9
48	Photoluminescence Studies of Sequentially Mg and H Ion-implanted GaN with Various Implantation Depths and Crystallographic Planes. , 2019, , .		1
49	In-plane optical polarization and dynamic properties of the near-band-edge emission of an m-plane freestanding AlN substrate and a homoepitaxial film. Applied Physics Letters, 2019, 115, 151903.	1.5	11
50	Two-dimensional analysis of the nonuniform quantum yields of multiple quantum wells for AlGaN-based deep-ultraviolet LEDs grown on AlN templates with dense macrosteps using cathodoluminescence spectroscopy. Journal of Applied Physics, 2019, 126, .	1.1	12
51	Carrier localization structure combined with current micropaths in AlGaN quantum wells grown on an AlN template with macrosteps. Applied Physics Letters, 2019, 114, .	1.5	37
52	An Outdoor Evaluation of 1-Gbps Optical Wireless Communication using AlGaN-based LED in 280-nm Band. , 2019, , .		3
53	Photocatalytic NO removal over calcium-bridged siloxenes under ultraviolet and visible light irradiation. Dalton Transactions, 2018, 47, 7070-7076.	1.6	9
54	Nearly temperature-independent ultraviolet light emission intensity of indirect excitons in hexagonal BN microcrystals. Journal of Applied Physics, 2018, 123, .	1.1	22

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55	Carrier Trapping by Vacancyâ€Type Defects in Mgâ€Implanted GaN Studied Using Monoenergetic Positron Beams. Physica Status Solidi (B): Basic Research, 2018, 255, 1700521.	0.7	60
56	The origins and properties of intrinsic nonradiative recombination centers in wide bandgap GaN and AlGaN. Journal of Applied Physics, 2018, 123, .	1.1	112
57	Determination of Deformation Potentials in InGaN Alloy Material for Theoretical Prediction of Optical Gain Characteristics in Semipolar and Nonpolar InGaN Quantum Wells Laser Diodes. , 2018, , .		1
58	Room-temperature photoluminescence lifetime for the near-band-edge emission of (0001Â¯) p-type GaN fabricated by sequential ion-implantation of Mg and H. Applied Physics Letters, 2018, 113, .	1.5	40
59	1.6-Gbps LED-Based Ultraviolet Communication at 280 nm in Direct Sunlight. , 2018, , .		9
60	Large electron capture-cross-section of the major nonradiative recombination centers in Mg-doped GaN epilayers grown on a GaN substrate. Applied Physics Letters, 2018, 112, .	1.5	55
61	Polarity-dependence of the defect formation in c-axis oriented ZnO by the irradiation of an 8â€‰MeV proton beam. Journal of Applied Physics, 2018, 123, 161562.	1.1	6
62	Effects of extra metals added in an autoclave during acidic ammonothermal growth of m-plane GaN single crystals using an NH₄F mineralizer. Applied Physics Express, 2018, 11, 091002.	1.1	10
63	A design strategy for achieving more than 90% of the overlap integral of electron and hole wavefunctions in high-AlN-mole-fraction AlxGa1âˆ’xN multiple quantum wells. Applied Physics Express, 2017, 10, 015802.	1.1	13
64	Ultraviolet light-absorbing and emitting diodes consisting of a p-type transparent-semiconducting NiO film deposited on an n-type GaN homoepitaxial layer. Applied Physics Letters, 2017, 110, .	1.5	20
65	A Low-Symmetry Cubic Mesophase of Dendronized CdS Nanoparticles and Their Structure-Dependent Photoluminescence. CheM, 2017, 2, 860-876.	5.8	27
66	Photocatalytic activity of silicon-based nanoflakes for the decomposition of nitrogen monoxide. Dalton Transactions, 2017, 46, 8643-8648.	1.6	11
67	Nitrogen vacancies as a common element of the green luminescence and nonradiative recombination centers in Mg-implanted GaN layers formed on a GaN substrate. Applied Physics Express, 2017, 10, 061002.	1.1	70
68	High temperature degradation mechanism of a red phosphor, CaAlSiN3:Eu for solid-state lighting. Journal of Applied Physics, 2017, 122, .	1.1	16
69	Demonstration of omnidirectional photoluminescence (ODPL) spectroscopy for precise determination of internal quantum efficiency of radiation in GaN single crystals. Applied Physics Letters, 2017, 111, .	1.5	12
70	Defectâ€Resistant Radiative Performance of mâ€Plane Immiscible Al_{1âˆ’}_xIn_xN Epitaxial Nanostructures for Deepâ€Ultraviolet and Visible Polarized Light Emitters. Advanced Materials, 2017, 29, 1603644.	11.1	38
71	Local structure around In atoms in coherently grownm-plane InGaN film. Journal of Synchrotron Radiation, 2017, 24, 1012-1016.	1.0	0
72	Phase transformation during simultaneous chalcogenization of CuIn(S,Se) ₂ thin films using metalorganic sources. Physica Status Solidi C: Current Topics in Solid State Physics, 2017, 14, 1600159.	0.8	0

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73	Determination of absolute value of quantum efficiency of radiation in high quality GaN single crystals using an integrating sphere. Journal of Applied Physics, 2016, 120, .	1.1	28
74	Electronic and optical characteristics of an m-plane GaN single crystal grown by hydride vapor phase epitaxy on a GaN seed synthesized by the ammonothermal method using an acidic mineralizer. Japanese Journal of Applied Physics, 2016, 55, 05FA03.	0.8	4
75	Electrical properties of undoped and Li-doped NiO thin films deposited by RF sputtering without intentional heating. Japanese Journal of Applied Physics, 2016, 55, 088003.	0.8	19
76	Controlling the carrier lifetime of nearly threading-dislocation-free ZnO homoepitaxial films by 3d transition-metal doping. Applied Physics Letters, 2016, 108, .	1.5	9
77	Spectroscopic ellipsometry studies on the m-plane Al_{1âˆ’} _xIn_xN epilayers grown by metalorganic vapor phase epitaxy on a freestanding GaN substrate. Japanese Journal of Applied Physics, 2016, 55, 05FG04.	0.8	6
78	Vacancies and electron trapping centers in acidic ammonothermal GaN probed by a monoenergetic positron beam. Journal of Crystal Growth, 2016, 448, 117-121.	0.7	22
79	Impacts of Dislocations and Point Defects on the Internal Quantum Efficiency of the Near-Band-Edge Emission in AlGaN-Based DUV Light-Emitting Materials. Springer Series in Materials Science, 2016, , 115-136.	0.4	2
80	Reduction in the concentration of cation vacancies by proper Si-doping in the well layers of high AlN mole fraction AlxGa1â€“xN multiple quantum wells grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2015, 107, 121602.	1.5	27
81	Spatio-time-resolved cathodoluminescence studies on the Si-doping effects in high AlN mole fraction AlxGa1âˆ’xN multiple quantum wells grown on an AlN template by metalorganic vapor phase epitaxy. , 2015, , .		0
82	Fabrication of visibleâ€light transparent solar cells composed of NiO/Ni_xZn_{1â€x}O/ZnO heterostructures. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 785-788.	0.8	21
83	Polarity dependent radiation hardness of GaN. , 2015, , .		0
84	Structural and optical properties of AlN grown by solid source solution growth method. Japanese Journal of Applied Physics, 2015, 54, 085501.	0.8	0
85	Local excitation and emission dynamics of an isolated single basal-plane stacking-fault in GaN studied by spatio-time-resolved cathodoluminescence. Japanese Journal of Applied Physics, 2015, 54, 030303.	0.8	3
86	Low-resistivitym-plane freestanding GaN substrate with very low point-defect concentrations grown by hydride vapor phase epitaxy on a GaN seed crystal synthesized by the ammonothermal method. Applied Physics Express, 2015, 8, 095501.	1.1	21
87	Homoepitaxial growth of ZnO films with reduced impurity concentrations by helicon-wave-excited-plasma sputtering epitaxy using a crystalline ZnO target prepared by hydrothermal technique. Japanese Journal of Applied Physics, 2014, 53, 100301.	0.8	2
88	High internal quantum efficiency ultraviolet to green luminescence peaks from pseudomorphic m-plane Al1âˆ’xInxN epilayers grown on a low defect density m-plane freestanding GaN substrate. Journal of Applied Physics, 2014, 116, .	1.1	24
89	Experimental determination of band offsets of NiO-based thin film heterojunctions. Journal of Applied Physics, 2014, 116, .	1.1	59
90	Preparation of CuInS2 thin films by sulfurization using ditertiarybutylsulfide. Thin Solid Films, 2014, 558, 400-404.	0.8	4

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91	Ammonothermal growth of GaN on a self-nucleated GaN seed crystal. Journal of Crystal Growth, 2014, 404, 168-171.	0.7	20
92	Polarized XAFS study of AlK-edge form-plane AlGaN films. Journal of Physics: Conference Series, 2014, 502, 012031.	0.3	1
93	Electronic Structure and Spontaneous Polarization in Sc_xAl_yGa_{1-x-y}N Alloys Lattice-Matched to GaN: A First-Principles Study. Japanese Journal of Applied Physics, 2013, 52, 08JM04.	0.8	1
94	Fabrication of Visible-Light-Transparent Solar Cells Using p-Type NiO Films by Low Oxygen Fraction Reactive RF Sputtering Deposition. Japanese Journal of Applied Physics, 2013, 52, 021102.	0.8	49
95	Excitonic emission dynamics in homoepitaxial AlN films studied using polarized and spatio-time-resolved cathodoluminescence measurements. Applied Physics Letters, 2013, 103, .	1.5	27
96	Acidic ammonothermal growth of GaN crystals using GaN powder as a nutrient. CrystEngComm, 2013, 15, 5382.	1.3	13
97	Ammonothermal Crystal Growth of GaN Using an NH₄F Mineralizer. Crystal Growth and Design, 2013, 13, 4158-4161.	1.4	52
98	Spatio-Time-Resolved Cathodoluminescence Studies on Freestanding GaN Substrates Grown by Hydride Vapor Phase Epitaxy. ECS Transactions, 2013, 50, 1-8.	0.3	2
99	Local carrier dynamics around the sub-surface basal-plane stacking faults of GaN studied by spatio-time-resolved cathodoluminescence using a front-excitation-type photoelectron-gun. Applied Physics Letters, 2013, 103, .	1.5	13
100	Time-resolved luminescence studies on AlN and high AlN mole fraction AlGaN alloys. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 501-506.	0.8	6
101	Impacts of Si-doping and resultant cation vacancy formation on the luminescence dynamics for the near-band-edge emission of Al0.6Ga0.4N films grown on AlN templates by metalorganic vapor phase epitaxy. Journal of Applied Physics, 2013, 113, .	1.1	98
102	Photoluminescence Study of Defect Levels in CuInS$_{2}$ Thin Films Grown by Sulfurization Using Ditertiarybutylsulfide. Japanese Journal of Applied Physics, 2012, 51, 031202.	0.8	6
103	Signatures of Î“₁â€“Î“₅mixed-mode polaritons in polarized reflectance spectra of ZnO. Journal of Physics Condensed Matter, 2012, 24, 415801.	0.7	5
104	Local lifetime and luminescence efficiency for the near-band-edge emission of freestanding GaN substrates determined using spatio-time-resolved cathodoluminescence. Applied Physics Letters, 2012, 101, .	1.5	14
105	Time-resolved photoluminescence, positron annihilation, and Al0.23Ga0.77N/GaN heterostructure growth studies on low defect density polar and nonpolar freestanding GaN substrates grown by hydride vapor phase epitaxy. Journal of Applied Physics, 2012, 111, .	1.1	67
106	Femtosecond-laser-driven photoelectron-gun for time-resolved cathodoluminescence measurement of GaN. Review of Scientific Instruments, 2012, 83, 043905.	0.6	15
107	Lateral transport properties of Nb-doped rutile- and anatase-TiO2 films epitaxially grown on c-plane GaN. Applied Physics Letters, 2012, 101, 072107.	1.5	5
108	Valence-band-ordering of a strain-free bulk ZnO single crystal identified by four-wave-mixing spectroscopy technique. Journal of Applied Physics, 2012, 111, 093522.	1.1	8

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109	Defect characterization in Mg-doped GaN studied using a monoenergetic positron beam. Journal of Applied Physics, 2012, 111, .	1.1	33
110	Exciton binding energies in chalcopyrite semiconductors. Physical Review B, 2012, 85, .	1.1	14
111	Structural, elastic, and polarization parameters and band structures of wurtzite ZnO and MgO. Journal of Applied Physics, 2012, 112, .	1.1	59
112	First-principles study of spontaneous polarization and band gap bowing in ScxAlyGa1 âˆ’xâˆ’yN alloys lattice-matched to GaN. Semiconductor Science and Technology, 2012, 27, 105014.	1.0	4
113	Powder synthesis and ammonothermal crystal growth of GaN from metallic Ga in the presence of NH4I. CrystEngComm, 2012, 14, 3351.	1.3	7
114	Advantages and remaining issues of state-of-the-artm-plane freestanding GaN substrates grown by halide vapor phase epitaxy form-plane InGaN epitaxial growth. Semiconductor Science and Technology, 2012, 27, 024008.	1.0	15
115	Photoluminescence Study of Defect Levels in CuInS₂Thin Films Grown by Sulfurization Using Ditertiarybutylsulfide. Japanese Journal of Applied Physics, 2012, 51, 031202.	0.8	0
116	Sulfurization growth of CuInS<inf>2</inf> thin films and solar cells using ditertiarybutylsulfide as a less-hazardous source. , 2011, , .		0
117	Growth of Cu(In,Al)(S,Se)2Thin Films by Selenization and Sulfurization for a Wide Bandgap Absorber. Japanese Journal of Applied Physics, 2011, 50, 05FB07.	0.8	1
118	Morphological and Structural Changes in Cu(In,Ga)Se2Thin Films by Selenization Using Diethylselenide. Japanese Journal of Applied Physics, 2011, 50, 05FB05.	0.8	6
119	Optical polarization properties of m-plane AlxGa_1-xN epitaxial films grown on m-plane freestanding GaN substrates toward nonpolar ultraviolet LEDs. Optics Express, 2011, 19, A1008.	1.7	5
120	Spontaneous polarization and band gap bowing in YxAlyGa1-x-yN alloys lattice-matched to GaN. Journal of Applied Physics, 2011, 110, 074114.	1.1	9
121	Point defects in GaN and related group-III nitrides studied by means of positron annihilation. Proceedings of SPIE, 2011, , .	0.8	4
122	Heliconâ€waveâ€excited plasma sputtering epitaxy of Nbâ€doped TiO₂ films on GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 534-536.	0.8	2
123	Implementation of Spatio-Time-Resolved Cathodoluminescence Spectroscopy for Studying Local Carrier Dynamics in a Low Dislocation Density m-Plane In_{0.05}Ga_{0.95}N Epilayer Grown on a Freestanding GaN Substrate. Japanese Journal of Applied Physics, 2011, 50, 111002.	0.8	12
124	Sulfurization Growth of CuInS2Thin Film Using Ditertiarybutylsulfide as a Less Hazardous Source. Japanese Journal of Applied Physics, 2011, 50, 065503.	0.8	7
125	Microstructure and interface control of GaN/MgAl2O4 grown by metalorganic chemical vapor deposition: Substrate-orientation dependence. Journal of Applied Physics, 2011, 110, 023504.	1.1	12
126	Impacts of anisotropic tilt mosaics of state-of-the-art m-plane freestanding GaN substrates on the structural and luminescent properties of m-plane AlxGa1âˆ’xN epilayers. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, .	0.6	5

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127	Transparent semiconducting Nb-doped anatase TiO2 films deposited by helicon-wave-excited-plasma sputtering. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 011017.	0.6	13
128	Collateral evidence for an excellent radiative performance of AlxGa1â^'xN alloy films of high AlN mole fractions. Applied Physics Letters, 2011, 99, 051902.	1.5	27
129	Time-Resolved Photoluminescence of a Two-Dimensional Electron Gas in an Al_{0.2}Ga_{0.8}N/GaN Heterostructure Fabricated on Ammonothermal GaN Substrates. Applied Physics Express, 2011, 4, 045501.	1.1	7
130	Morphological and Structural Changes in Cu(In,Ga)Se₂Thin Films by Selenization Using Diethylselenide. Japanese Journal of Applied Physics, 2011, 50, 05FB05.	0.8	4
131	Growth of Cu(In,Al)(S,Se)₂Thin Films by Selenization and Sulfurization for a Wide Bandgap Absorber. Japanese Journal of Applied Physics, 2011, 50, 05FB07.	0.8	4
132	Sulfurization Growth of CuInS₂Thin Film Using Ditertiarybutylsulfide as a Less Hazardous Source. Japanese Journal of Applied Physics, 2011, 50, 065503.	0.8	3
133	Implementation of Spatio-Time-Resolved Cathodoluminescence Spectroscopy for Studying Local Carrier Dynamics in a Low Dislocation Densitym-Plane In0.05Ga0.95N Epilayer Grown on a Freestanding GaN Substrate. Japanese Journal of Applied Physics, 2011, 50, 111002.	0.8	0
134	Crystal Phase-Selective Epitaxy of Rutile and Anatase Nb-Doped TiO2Films on a GaN Template by the Helicon-Wave-Excited-Plasma Sputtering Epitaxy Method. Applied Physics Express, 2010, 3, 091102.	1.1	14
135	Light polarization characteristics of m-plane AlxGa1â^'xN films suffering from in-plane anisotropic tensile stresses. Journal of Applied Physics, 2010, 107, .	1.1	12
136	Photoluminescence and positron annihilation studies on Mg-doped nitrogen-polarity semipolar (101Â¯1Â¯) GaN heteroepitaxial layers grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2010, 96, 091913.	1.5	9
137	Major impacts of point defects and impurities on the carrier recombination dynamics in AlN. Applied Physics Letters, 2010, 97, .	1.5	31
138	Surface stoichiometry and activity control for atomically smooth low dislocation density ZnO and pseudomorphic MgZnO epitaxy on a Zn-polar ZnO substrate by the helicon-wave-excited-plasma sputtering epitaxy method. Journal of Applied Physics, 2010, 108, .	1.1	21
139	Identification of extremely radiative nature of AlN by time-resolved photoluminescence. Applied Physics Letters, 2010, 96, .	1.5	28
140	Interface chemistry and electronic structure of GaN/MgAl2O4 revealed by angle-resolved photoemission spectroscopy. Applied Physics Letters, 2010, 97, 161907.	1.5	8
141	Optimization of the Growth Conditions for Molecular Beam Epitaxy of Mg_xZn_{1-x}O (0â‰xâ‰0.12) Films on Zn-Polar ZnO Substrates. Japanese Journal of Applied Physics, 2010, 49, 071104.	0.8	15
142	Optical and Solar Cell Properties of Alpha-ray, Proton, and Gamma-ray Irradiated Cu(In,Ga)Se₂ Thin Films and Solar Cells. Japanese Journal of Applied Physics, 2010, 49, 042302.	0.8	18
143	Nitrogen doped MgxZn1â^'xO/ZnO single heterostructure ultraviolet light-emitting diodes on ZnO substrates. Applied Physics Letters, 2010, 97, .	1.5	184
144	Optical Properties of GaN Substrates. Springer Series in Materials Science, 2010, , 277-293.	0.4	0

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145	Vacancy-oxygen complexes and their optical properties in AlN epitaxial films studied by positron annihilation. Journal of Applied Physics, 2009, 105, .	1.1	63
146	Free and bound exciton fine structures in AlN epilayers grown by low-pressure metalorganic vapor phase epitaxy. Journal of Applied Physics, 2009, 105, .	1.1	45
147	Impacts of anisotropic lattice relaxation on crystal mosaicity and luminescence spectra of m-plane AlxGa1â^'xN films grown on m-plane freestanding GaN substrates by NH3 source molecular beam epitaxy. Applied Physics Letters, 2009, 94, .	1.5	9
148	Structural, Optical, and Homoepitaxial Studies on the Bulk GaN Single Crystals Spontaneously Nucleated by the Na-Flux Method. Applied Physics Express, 2009, 2, 091004.	1.1	0
149	Thermal stability of semi-insulating property of Fe-doped GaN bulk films studied by photoluminescence and monoenergetic positron annihilation techniques. Journal of Applied Physics, 2009, 105, 083542.	1.1	24
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